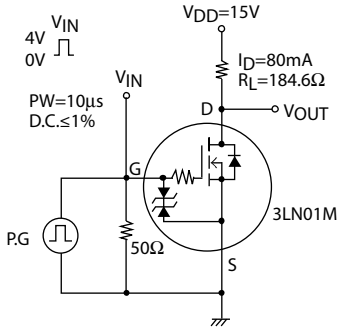
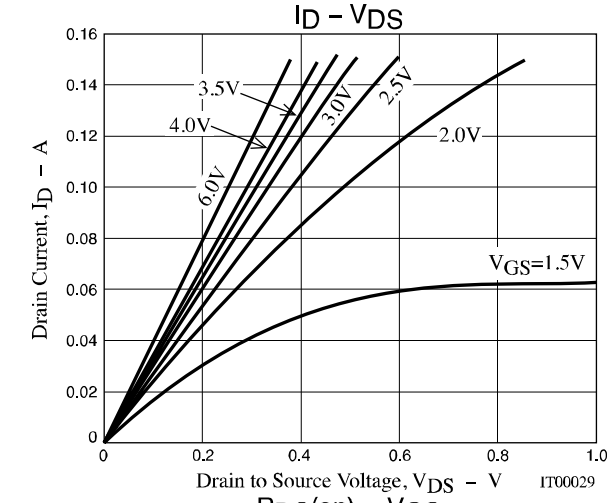
Continued from preceding page.

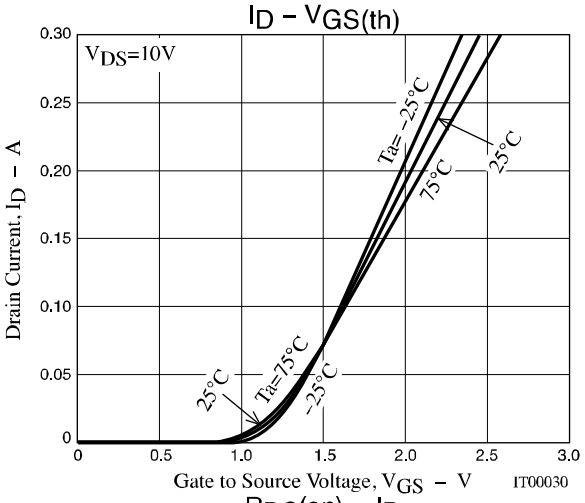
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Static Drain to Source On-State Resistance	$R_{DS}(on)1$	I_D=80mA, V_{GS}=4V		2.9	3.7	Ω
	$R_{DS}(on)2$	I_D=40mA, V_{GS}=2.5V		3.7	5.2	Ω
	$R_{DS}(on)3$	I_D=10mA, V_{GS}=1.5V		6.4	12.8	Ω
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		7.0		pF
Output Capacitance	Coss			5.9		pF
Reverse Transfer Capacitance	Crss			2.3		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		19		ns
Rise Time	t_r			65		ns
Turn-OFF Delay Time	$t_d(off)$			155		ns
Fall Time	t_f			120		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=150mA		1.58		nC
Gate to Source Charge	Qgs			0.26		nC
Gate to Drain “Miller” Charge	Qgd			0.31		nC
Forward Diode Voltage	V_{SD}	I_S=150mA, V_{GS}=0V		0.87	1.2	V

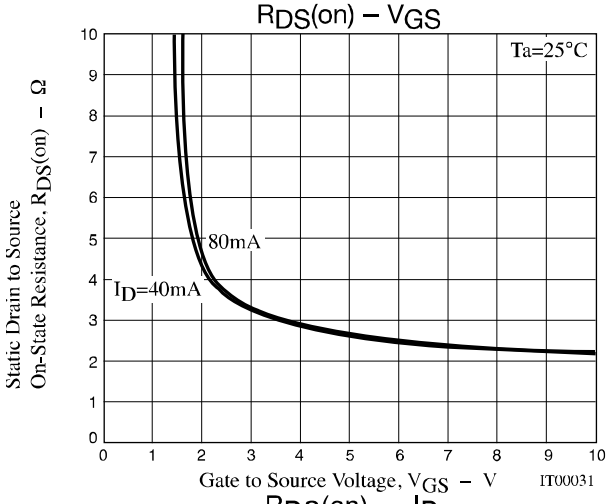
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

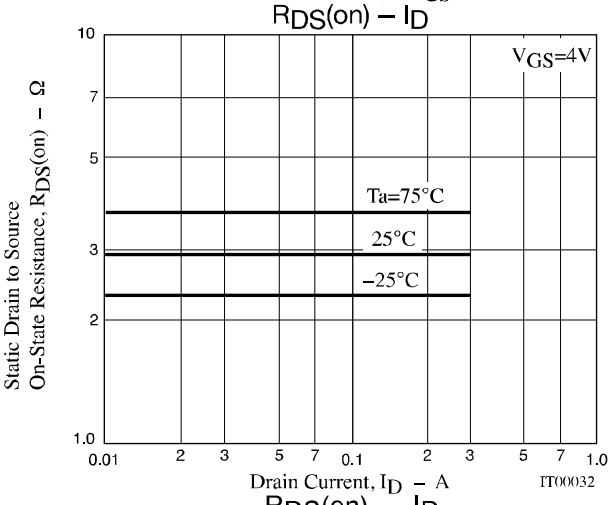
Switching Time Test Circuit

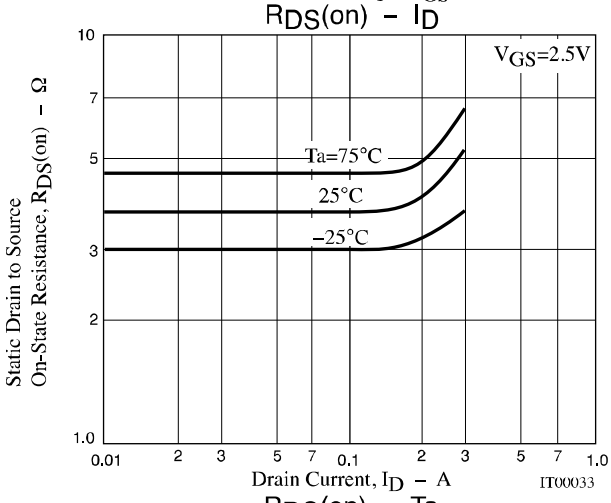


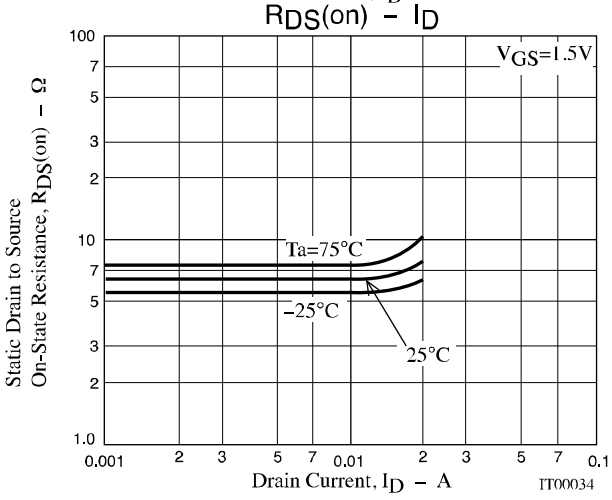


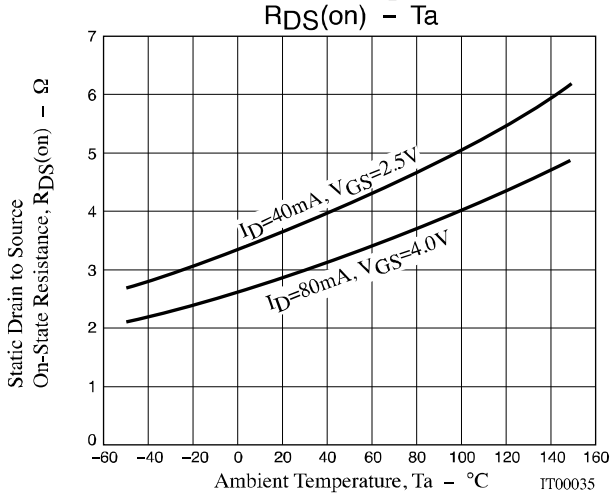


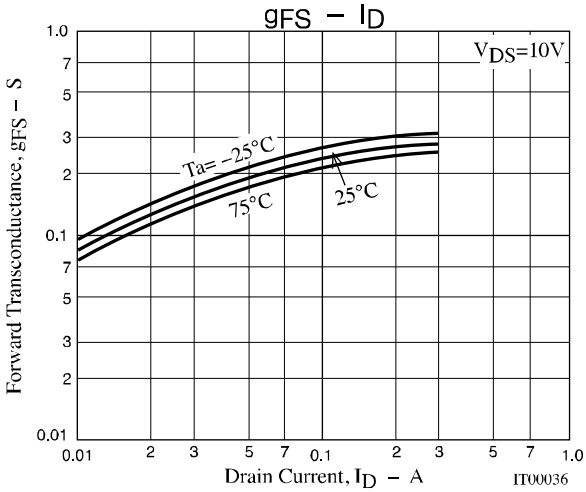


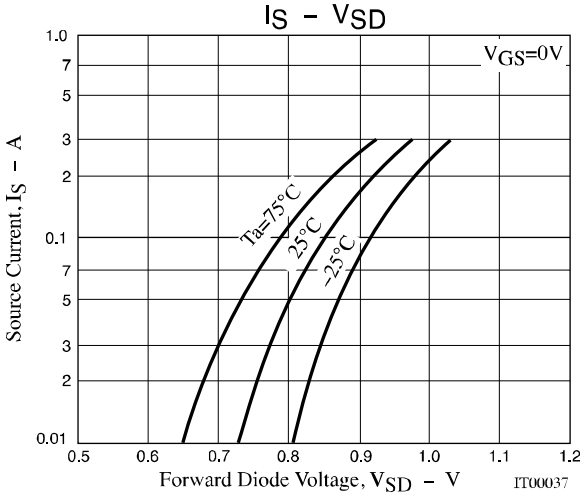


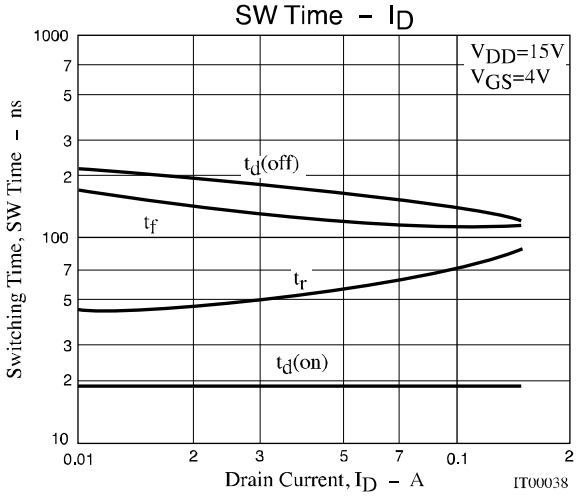


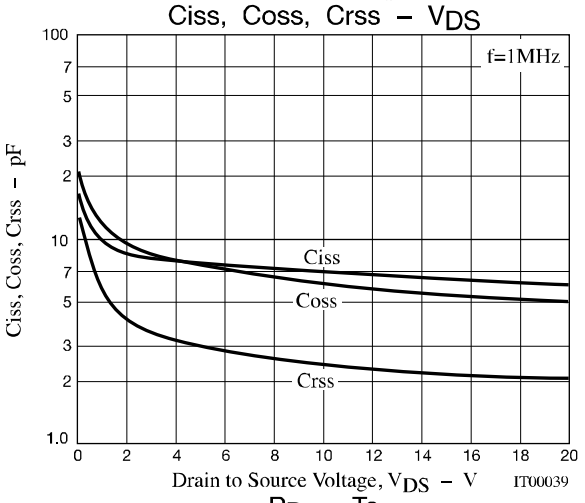


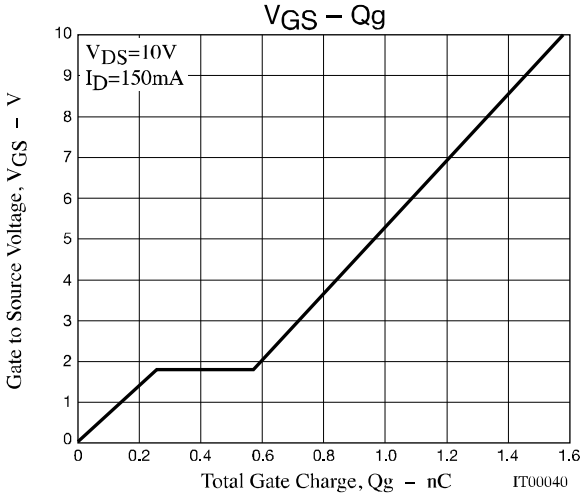


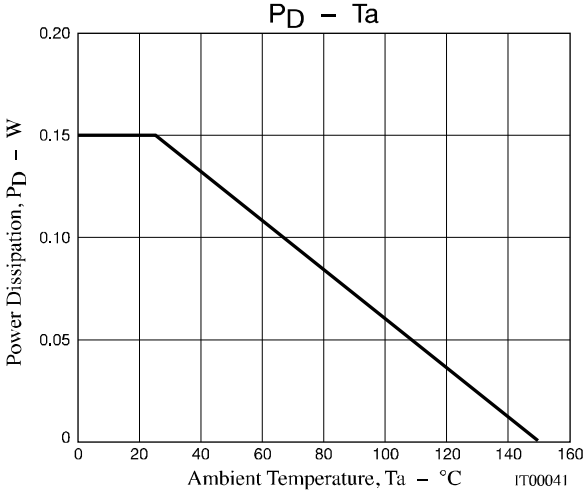












Package Dimensions

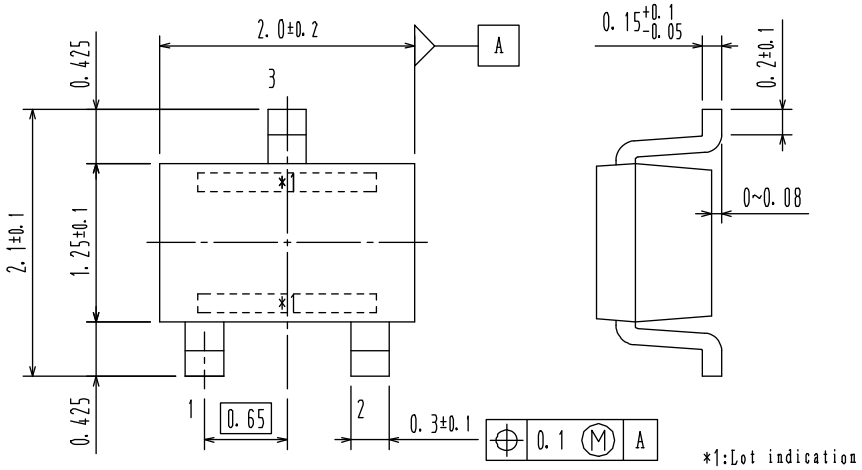
3LN01M-TL-E/ 3LN01M-TL-H

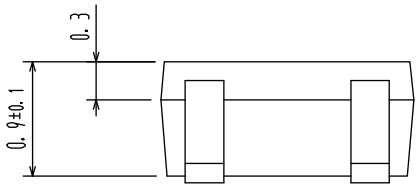
SC-70/MCP3

CASE 419AJ
ISSUE O

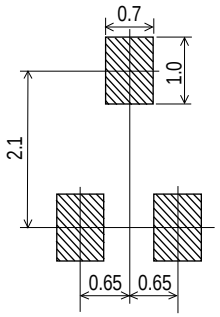
Unit : mm

1 : Gate
2 : Source
3 : Drain





Recommended Soldering Footprint



ORDERING INFORMATION

Device	Package	Shipping	Note
3LN01M-TL-E	MCP3 SC-70,SOT-323	3,000 pcs. / reel	Pb-Free
3LN01M-TL-H			Pb-Free and Halogen Free

Note on usage : Since the 3LN01M is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.